L Number	Hits	Search Text	DB	Time stamp
- Number	1	"6642092"	USPAT	2004/03/30 11:54
-	1	"6647946"	USPAT	2004/03/30 12:04
-	606	438/151.ccls.	USPAT	2004/03/30 12:04
-	322	438/151.ccls. and TFT	USPAT	2004/03/30 12:04
-	9	438/151.ccls. and TFT and foil	USPAT	2004/03/30 12:05
-	9	substrate	USPAT	2004/03/30 12:05
-	8	438/151.ccls. and TFT and foil and substrate and electrical	USPAT	2004/03/30 12:17
-	4	438/151.ccls. and TFT and foil and substrate and electrical and isolat\$4	USPAT	2004/03/30 12:17
-	4	substrate and electrical and isolat\$4 and	USPAT	2004/03/30 12:17
-	4	substrate and electrical and isolat\$4 and	USPAT	2004/03/30 12:17
-	4	substrate and electrical and isolat\$4 and	USPAT	2004/03/30 12:17
-	4	substrate and electrical and isolat\$4 and	USPAT	2004/03/30 12:17
-	3	layer and drain and source and channel 438/151.ccls. and TFT and foil and substrate and electrical and isolat\$4 and layer and drain and source and channel	USPAT	2004/03/30 12:18
_	3	and polycrystalline 438/151.ccls. and TFT and foil and substrate and electrical and isolat\$4 and	USPAT	2004/03/30 12:18
_	3	layer and drain and source and channel and polycrystalline and silicon 438/151.ccls. and TFT and foil and substrate and electrical and isolat\$4 and layer and drain and source and channel	USPAT	2004/03/30
_	0	and polycrystalline and silicon and gate 438/151.ccls. and TFT and foil and substrate and electrical and isolat\$4 and layer and drain and source and channel	USPAT	2004/03/30 12:18
_	0	and polycrystalline and silicon and gate and index 438/151.ccls. and TFT and foil and substrate and electrical and isolat\$4 and layer and drain and source and channel and polycrystalline and silicon and gate	USPAT	2004/03/30 12:19
-	3	and refract\$4 438/151.ccls. and TFT and foil and substrate and electrical and isolat\$4 and layer and drain and source and channel and polycrystalline and silicon and gate	USPAT	2004/03/31 07:24
_	0	and oxide "index of refraction"	USPAT.	2004/03/30
-	0	438/151.ccls. and TFT and foil and substrate and electrical and isolat\$4 and layer and drain and source and channel	USPAT	2004/03/31 07:37
		and polycrystalline and silicon and gate and oxide and refract\$4		2004/03/33
_		438/151.ccls. and refract\$4	USPAT	2004/03/31 07:37 2004/03/31
_	30	438/151.ccls. and refract\$4 and TFT 438/151.ccls. and refract\$4 and TFT and	USPAT	07:37
_	2	foil	USPAT	07:37 2004/03/31
_	2	foil and substrate		07:37

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-	1	438/151.ccls. and refract\$4 and TFT and	USPAI	07:38
		foil and substrate and electrical	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
-	0	438/151.ccls. and refract\$4 and TFT and	USPAT	2004/03/31
		foil and substrate and electrical and		07:38
		isolat\$4		
-	1	438/151.ccls. and refract\$4 and TFT and	USPAT	2004/03/31
		foil and substrate and electrical and		07:38
		drain		
l –	1	438/151.ccls. and refract\$4 and TFT and	USPAT	2004/03/31
		foil and substrate and electrical and		07:38
		drain and source		
_	1	438/151.ccls. and refract\$4 and TFT and	USPAT	2004/03/31
	_	foil and substrate and electrical and		07:38
		drain and source and channel		
_	l 0	438/151.ccls. and refract\$4 and TFT and	USPAT	2004/03/31
		foil and substrate and electrical and		07:39
		drain and source and channel and		
		polycrystalline		1
l <u>-</u>	1		USPAT	2004/03/31
	1	foil and substrate and electrical and		07:39
		drain and source and channel and silicon		
_	1	438/151.ccls. and refract\$4 and TFT and	USPAT	2004/03/31
	*	foil and substrate and electrical and		07:39
		drain and source and channel and silicon		
		and gate		
	1	438/151.ccls. and refract\$4 and TFT and	USPAT	2004/03/31
-	1	foil and substrate and electrical and		07:39
		drain and source and channel and silicon		
1	l .	and gate and oxide	<u> </u>	.l

## **WEST Search History**

Hide Items Restore Clear Cancel

DATE: Thursday, April 01, 2004

Hide?		Query	<u>Hit</u> Coun
	DB=PC	GPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD; PLUR=YES; OP=OR	
	L3	L1 and foil	
	L2	L1 and foil	
	L1	TFT and (titanium or steel or Kovar) and flex\$4 and (gate with oxide) and (polycrystalline or polysilicon)	3 .

END OF SEARCH HISTORY

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